

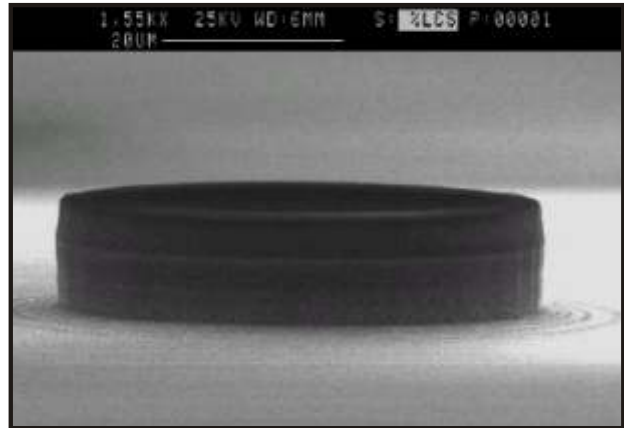
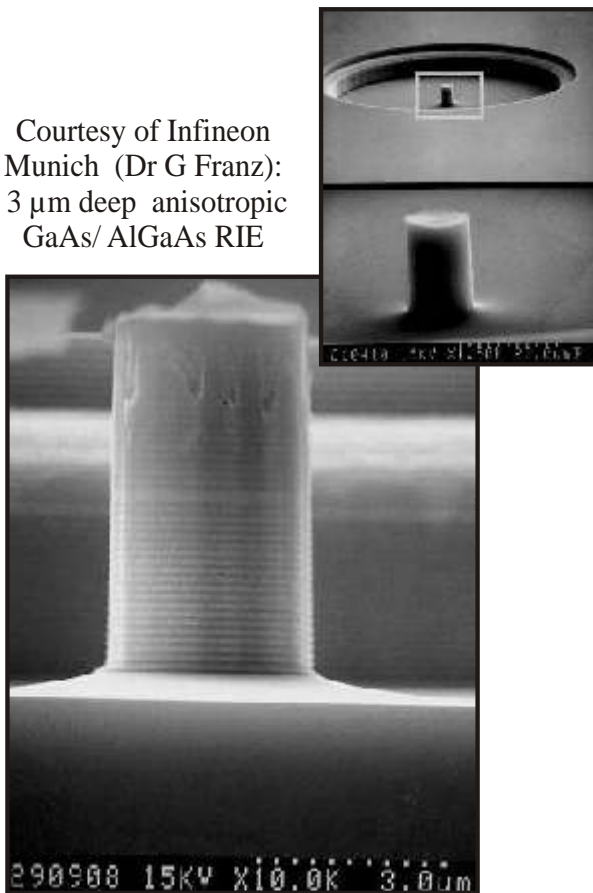


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 email: plasma@oxford.de

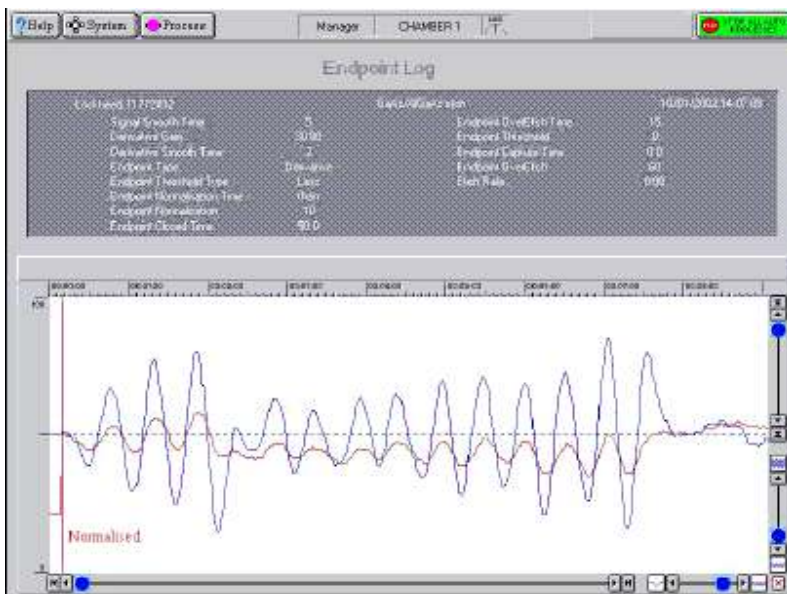
Plasmalab Data

VCSEL RIE of GaAs/ AlGaAs Heterostructures

Courtesy of Infineon Munich (Dr G Franz):
 3 μm deep anisotropic GaAs/ AlGaAs RIE



OPT application lab:
 8 μm deep anisotropic GaAs/ AlGaAs RIE on InGaAs using the laser interferometer



Plasmalab 80 Plus

Plasmalab System 100

Plasmalab System 133



- rate 50 - 150 nm/ min
- selectivity 1 : 1
- smooth walls
- wall angle > 89°
- mask: photoresist or SiO₂, Si₃N₄
- selectivity to PR > 5 : 1
- selectivity to SiO, SiN > 10: 1
- uniformity +/- 3 %